

## Design of a DAB Converter

The dual active bridge (DAB) converter is shown in Fig. 1. The converter operates with phase-shift modulated control, as shown in Fig. 1. Consider the following design of the converter:

- $V_g = 100$  V
- $V = 100$  V
- $n_t = 1$
- $f_s = 1$  MHz
- All devices  $Q_1$ - $Q_8$  have an effective output capacitance of  $C_{ds} = 200$  pF
- $C_{out}$  is very large

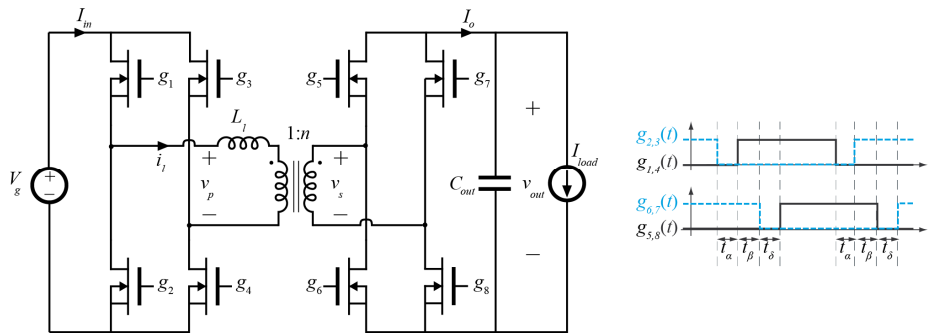


Figure 1: DAB converter

1. Sketch the  $j_l$ - $m_p$  and  $j_l$ - $m_s$  state planes for operation at  $P_{out}$  large enough such that all devices obtain ZVS and the phase shift  $t_\beta > 0$ . Solve the state planes for a set of equations describing circuit operation; complete the averaging step to solve for the normalized average output current,  $J$ .
2. Solve an expression for the normalized RMS output current  $J_{rms}$  (Note: see Appendix A.2 of *Fundamentals of Power Electronics*).
3. Manipulate the equations from (1) so that you obtain a single equation of the form:

$$J = f(F, J_{pk})$$

Plot the resulting equation on  $J_{pk}$ - $J$  axes, for  $F = 0.1$  0.5 and 1. Plot only the values of  $J_{pk}$  over which this solution is valid.

4. Design the tank (i.e. select  $L_l$ ) so that minimum conduction losses occur while maintaining ZVS down to an output power of  $P_{min} = 50$  W. What is  $F$ ?
5. What is the maximum power that can be delivered to the load with the design from (4)?

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The following devices are available for implementing  $Q_1$ - $Q_8$

	$R_{ds,on}$ [m $\Omega$ ]	$C_{ds}$ [pF]	$V_{bv}$ [V]
MOSFET A	100	200	200
MOSFET B	15	4000	200
MOSFET C	50	400	200
MOSFET D	500	40	200

For each MOSFET,  $L_l$  is designed so that  $P_{min} = 50$  W. You may assume that conduction losses can be modeled by the ideal rms currents solved for in (2).

6. Which MOSFET results in the smallest losses in-circuit, when operated at  $P_{out} = 50$  W?